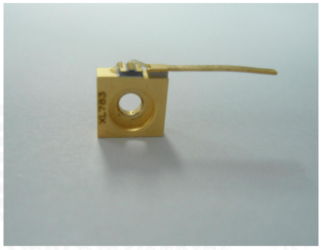
808nm Laser Diode

Features

Output Power: 3000mW (CW)

Efficient Quantum Well Structure

Standard C-Mount Package



Absolute Maximum Ratings

(Tc=25℃)

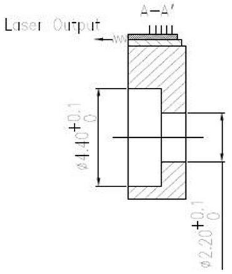
Item	Symbol	Absolute Maximum Ratings	Unit
Optical Output Power	Po	3000	mW
LD Reverse Voltage	Vr (LD)	2.5	V
Storage Temperature	Tstg	-20-80	℃
Operating Case Temperature	Tc	15~30	℃

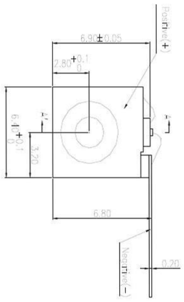
Initial Electrical/Optical Characteristics

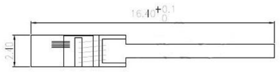
(Tc=25℃)

Item	**Symbol**	**Typ.**	**Unit**
Optical Output	Po	3000	mW
Peak Wavelength*	λp	808±3	nm
Threshold Current	Ith	0.4	A
Operating Current	Iop	3	A
Slope Efficiency	η	≥1.2	W/A
Operating Voltage	Vop	1.8	V
Horizontal Beam Divergence	θ//	8	deg.
Vertical Beam Divergence	θ⊥	36	deg.
Polarization		TE	

Outline Dimension







(Unit: mm)

* Measuring specifications.

All figures in this specification are measured by CNI's method and may contain measurement deviations

The above specifications are for reference purpose only and subjected to change without prior notice.

AVOID EXPOSURE-LASER RADIATION IS EMITTED FROM THIS APERTURE

DANGER

LASER RADIATION-AVOID EYE OR SKIN EXPOSURE TO DIRECT OR SCATTERED RADIATION

Maximum Output: 3W Wavelength:700-1000 nm

CLASS IV LASER PRODUCT

This device complies with 21 CFR 1040.10 and 1040.11
Changchun New Industries Optoelectronics Tech. Co., Ltd.
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